SUBSTRATE PROCESSING METHOD AND SUBSTRATE PROCESSING APPARATUS

ABSTRACT

A substrate processing method includes: providing a substrate including a silicon-containing film in a chamber; supplying a processing gas including HF gas into the chamber; etching the silicon-containing film with plasma generated from the processing gas, thereby forming a recess in the silicon-containing film; and controlling a partial pressure of the HF gas to decrease the partial pressure of the HF gas with an increase of an aspect ratio of the recess.

Fig. 7